STR1P2UH7

P-channel 20 V, 0.087 Ω typ., 1.4 A STripFET™ H7 Power MOSFET in a SOT-23 package

Datasheet - production data

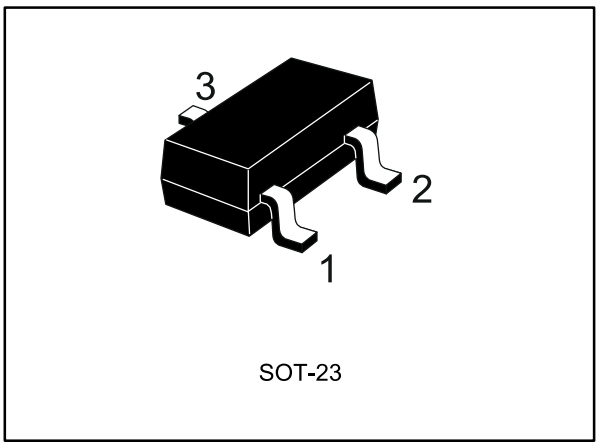
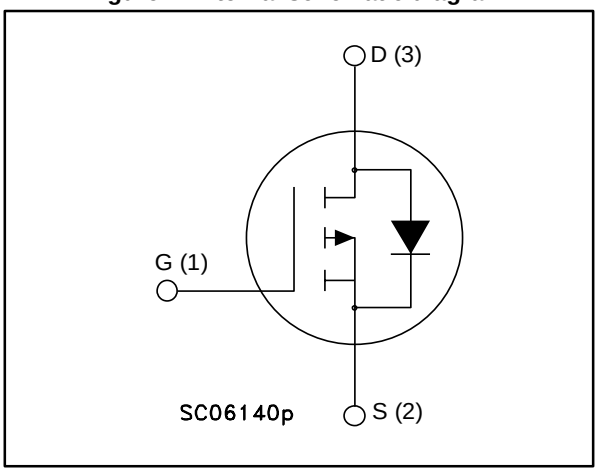


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STR1P2UH7	20 V	0.1 Ω @ 4.5	1.4 A

- Very low on-resistance
- Very low capacitance and gate charge
- High avalanche ruggedness

Applications

- Switching applications

Description

This P-channel Power MOSFET utilizes the STripFET H7 technology with a trench gate structure combined with extremely low on-resistance. The device also offers ultra-low capacitances for higher switching frequency operations.

Table 1: Device summary

Order code	Marking	Package	Packaging
STR1P2UH7	1L2U	SOT-23	Tape and reel

For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	20	V
V_{GS}	Gate-source voltage	± 8	V
I_D	Drain current (continuous) at T_{pcb} = 25 °C	1.4	A
I_D	Drain current (continuous) at T_{pcb} = 100 °C	0.9	A
I_{DM}(1)	Drain current (pulsed)	5.6	A
P_{TOT}	Total dissipation at T_{pcb} = 25 °C	0.35	W
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

Notes:

(1)Pulse width limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb max, single operation	357	°C/W

Notes:

(1)When mounted on 1inch² FR-4 board, 2 oz Cu

For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250 µA, V_{GS} = 0	20			V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 20 V, V_{GS} = 0			1	µA
I_{GSS}	Gate-body leakage current	V_{GS} = ± 8 V, V_{DS} = 0			10	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.4		1	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 4.5 V, I_D = 0.7 A		0.087	0.1	Ω
		V_{GS} = 2.5 V, I_D = 0.7 A		0.11	0.13	Ω
		V_{GS} = 1.8 V, I_D = 0.7 A		0.145	0.18	Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 10 V, f = 1 MHz, V_{GS} = 0	-	510	-	pF
C_{oss}	Output capacitance		-	66	-	pF
C_{rss}	Reverse transfer capacitance		-	44	-	pF
Q_g	Total gate charge	V_{DD} = 10 V, I_D = 3 A, V_{GS} = 4.5 V (see *Figure 14: "Gate charge test circuit"*)	-	4.8	-	nC
Q_{gs}	Gate-source charge		-	0.7	-	nC
Q_{gd}	Gate-drain charge		-	0.8	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 10 V, I_D = 1.5 A, R_G = 4.7 Ω, V_{GS} = 4.5 V (see *Figure 15: "Test circuit for inductive load switching and diode recovery times"*)	-	9	-	ns
t_r	Rise time		-	21	-	ns
$t_{d(off)}$	Turn-off delay time		-	40	-	ns
t_f	Fall time		-	19	-	ns

For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD}(1)	Forward on voltage	I_{SD} = 1 A, V_{GS} = 0	-	-	1	V
t_{rr}	Reverse recovery time	V_{DD} = 10 V di/dt = 100 A/µs, I_{SD} = 1 A T_j = 150 °C (see *Figure 15: "Test circuit for inductive load switching and diode recovery times"*)	-	12.5		ns
Q_{rr}	Reverse recovery charge		-	5		nC
I_{RRM}	Reverse recovery current		-	0.8		A

Notes:

(1)Pulsed: pulse duration = 300 µs, duty cycle 1.5%.

For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

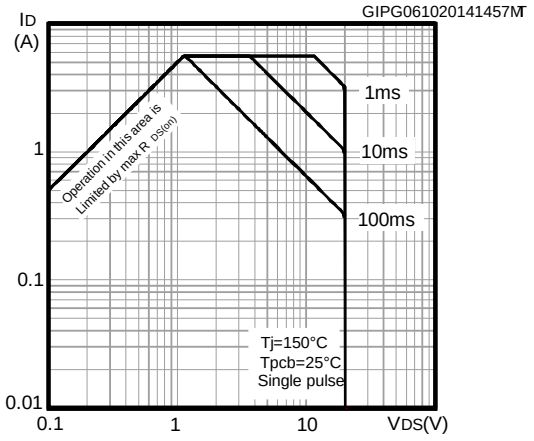


Figure 3: Thermal impedance

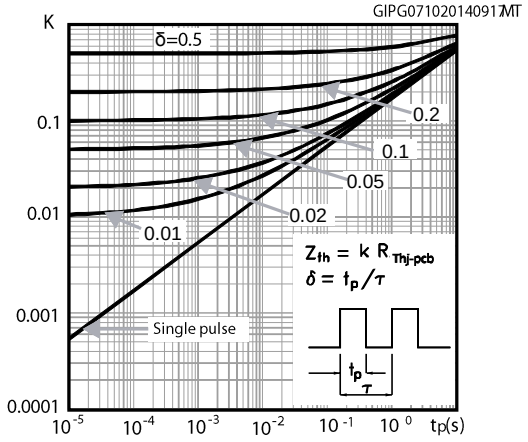


Figure 4: Output characteristics

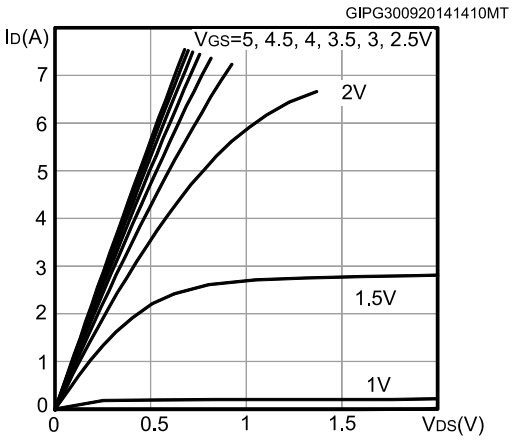


Figure 5: Transfer characteristics

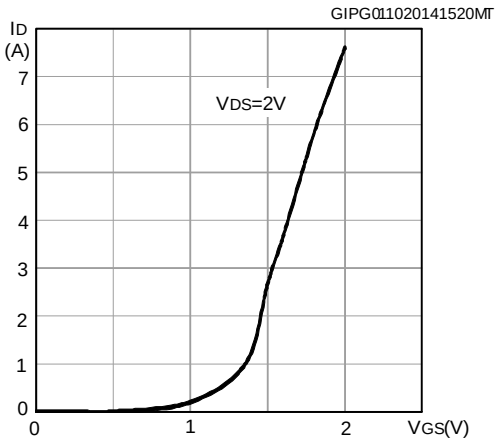


Figure 6: Gate charge vs gate-source voltage

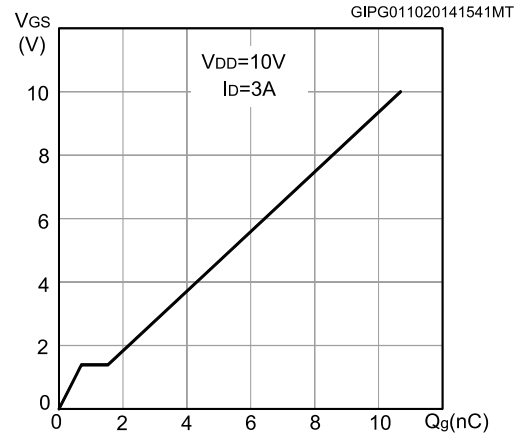


Figure 7: Static drain-source on-resistance

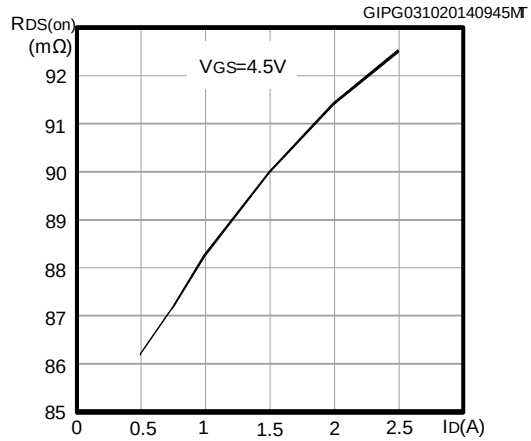


Figure 8: Capacitance variations

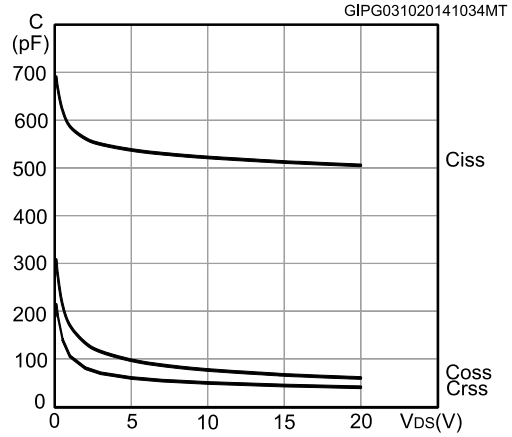


Figure 9: Normalized gate threshold voltage vs temperature

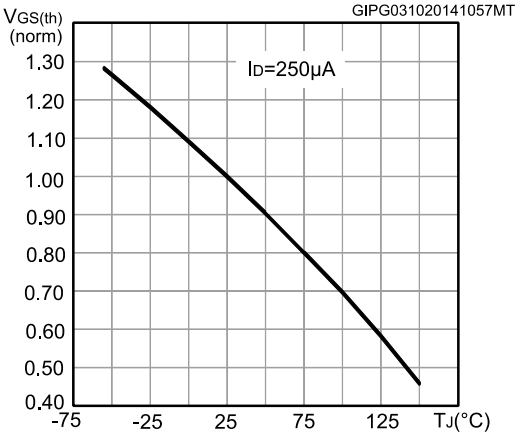


Figure 10: Normalized on-resistance vs temperature

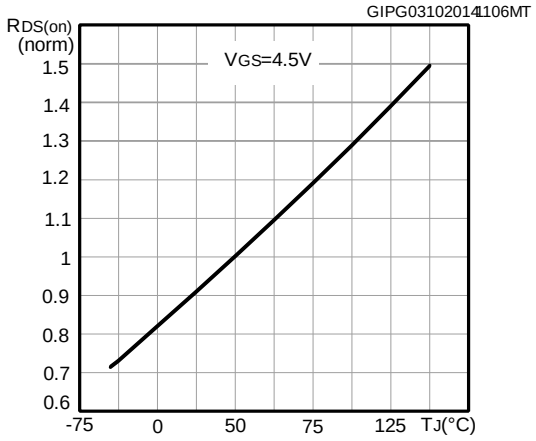


Figure 11: Normalized V(BR)DSS vs temperature

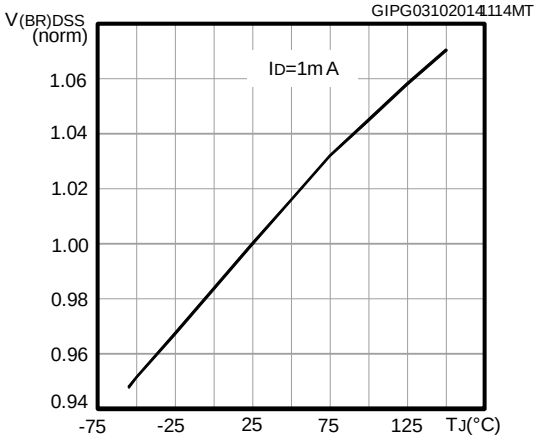
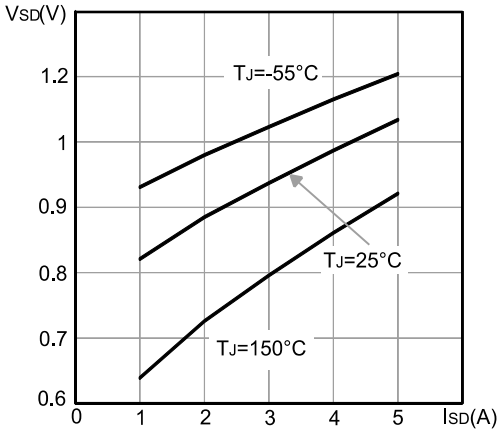


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Switching times test circuit for resistive load

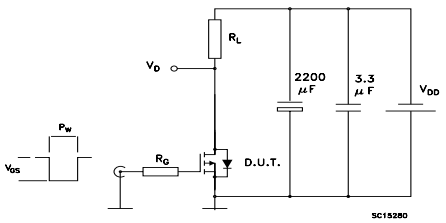


Figure 14: Gate charge test circuit

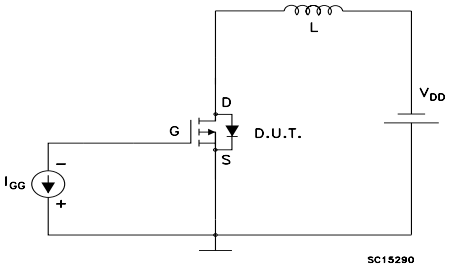
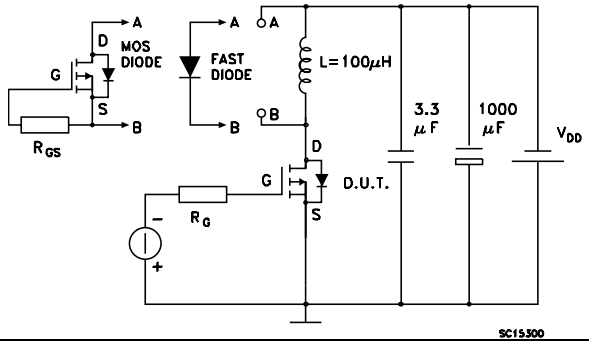


Figure 15: Test circuit for inductive load switching and diode recovery times



4 Package mechanical data

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4.1 SOT-23 package mechanical data

Figure 16: SOT-23 mechanical drawing

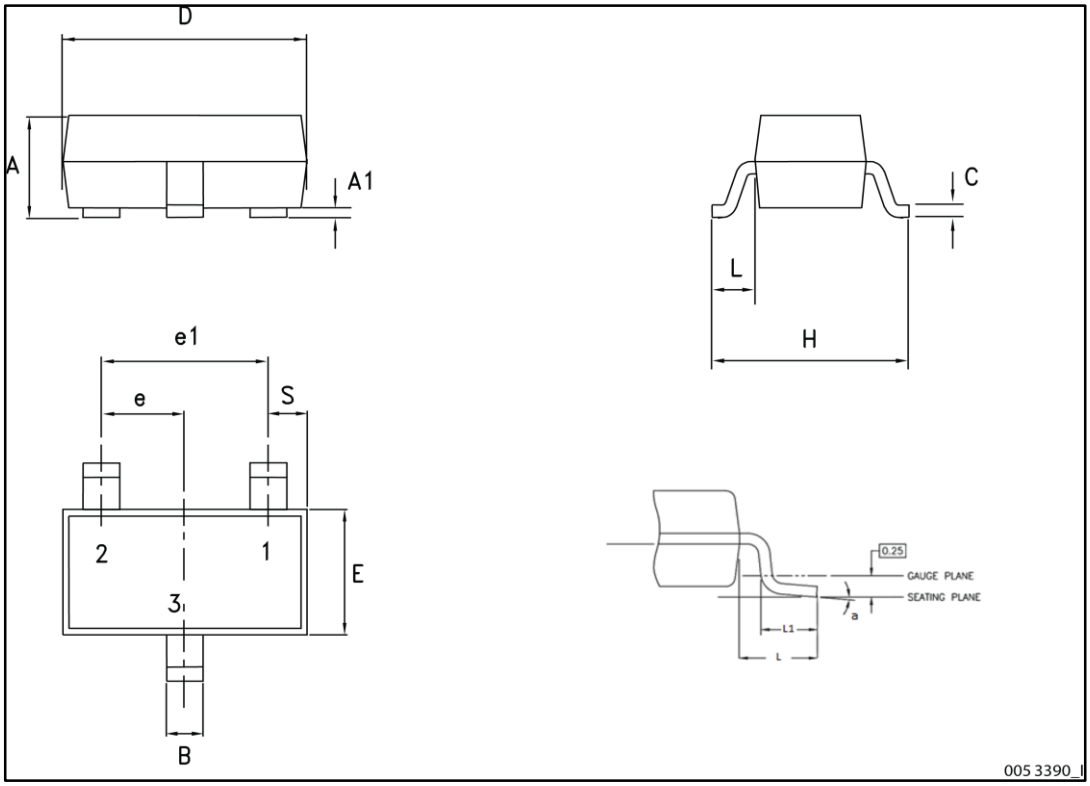
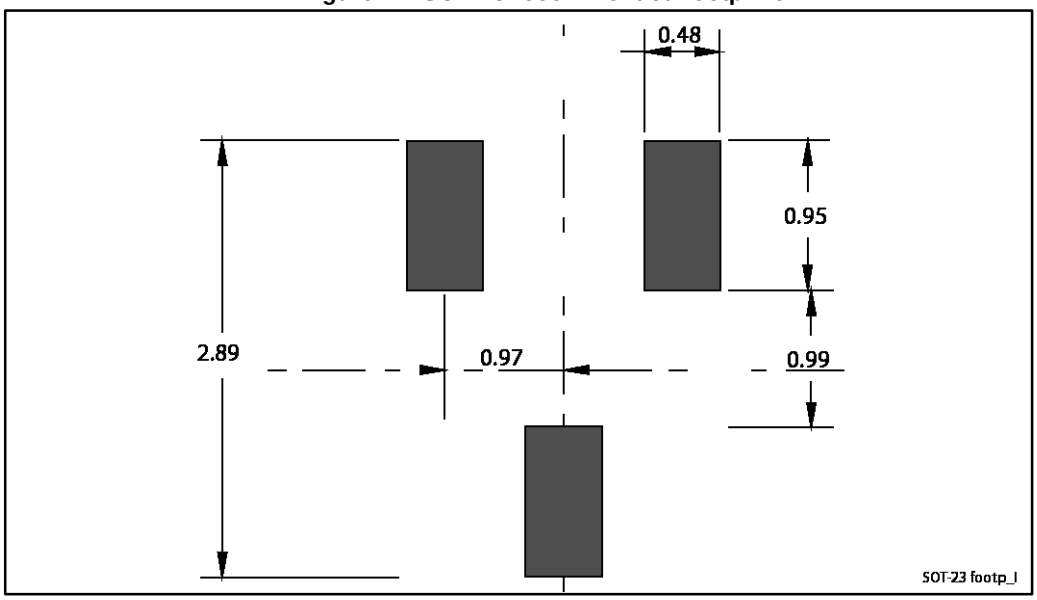


Table 8: SOT-23 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.89		1.40
A1	0		0.10
B	0.30		0.51
C	0.085		0.18
D	2.75		3.04
e	0.85		1.05
e1	1.70		2.10
E	1.20		1.75
H	2.10		3.00
L		0.60	
S	0.35		0.65
L1	0.25		0.55
a	0°		8°

Figure 17: SOT-23 recommended footprint



Dimensions are in mm.

5 Revision history

Table 9: Document revision history

Date	Revision	Changes
18-Jul-2013	1	First release.
07-Oct-2014	2	Document status promoted from target data to preliminary data. Updated title, features and description in cover page. Updated *Section 2: "Electrical characteristics"*. Minor text changes.
05-Jun-2015	3	Document status promoted from preliminary to production data.

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